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Low-Dimensional Systems

Raman and infrared spectroscopy of GaN nanocrystals grown by chloride-hydride vaporphase epitaxy on oxidized silicon

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Abstract Raman and infrared spectroscopy were applied to study nanocrystalline GaN films grown by chloride-hydride vapor-phase epitaxy on SiO₂/Si(111) substrates at T=520°C. It was ascertained that GaN nanocrystals are formed on the oxidized silicon surface at a rate of 10^{-2} nm/s. It was shown that the peaks in the Raman spectra $E_2(high)=566$ cm⁻¹ and $A_1(LO)=730$ cm⁻¹ correspond to the elastically strained GaN wurtzite structure. It was detected that a peak related to $E_1(TO)=558$ cm⁻¹ arises in the infrared spectra, which shows that elastic stresses in the nanocrystals are insignificant.

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